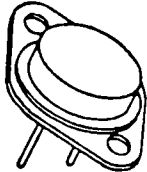


SPT420	SSDI
NPN HIGH VOLTAGE HIGH SPEED POWER TRANSISTOR 40 AMPS, 1000V	14830 VALLEY VIEW LA MIRADA, CA.90638 (213)921-9660 TWX 910-583-4807 FAX 213-921-2396

CASE STYLE

JEDEC TO-3 with .060 pins



FEATURES

- ▶ VERY FAST SWITCHING SPEED (100KHz)
- ▶ HIGH VOLTAGE (1000V)
- ▶ LOW VCE (SAT) AT IC = 20A
- ▶ HIGH CURRENT REPLACEMENT FOR 2N6678, 2N6921A
- ▶ EXTENDED RBSOA

MAXIMUM RATINGS

RATING	SYMBOL	VALUE	UNIT
Collector-Emitter Voltage	VCEO	450	Volts
Collector-Base Voltage	VCBO	1000	Volts
Emitter-Base Voltage	VEBO	10	Volts
Peak Collector Current	IC	60	Amps
Base Current	IB	6	Amps
Total Device Dissipation @ Tc = 25°C	PD	175	Watts
Derate Above 25°C		1	W/°C
Operating and Storage Temperature	TJ, Tstg	-65 to +200	°C

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	VALUE	UNIT
Thermal Resistance, Junction to Case	RθJC	0.63	°C/W

ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Min	Max	Unit
Collector-Emitter Breakdown Voltage* (IC = 200 mAdc)	BVCEO	450	-	Volts
Collector-Base Breakdown Voltage (IC = 200 μAdc)	BVCBO	1000	-	Volts

ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Min	Max	Unit	
Emitter-Base Breakdown Voltage ($I_E = 500 \text{ mA}$)	BVEBO	10	-	Vdc	
Collector Cutoff Current ($V_{CB} = 850 \text{ Vdc}$)	ICBO	-	1	μA	
Emitter Cutoff Current ($V_{EB} = 5 \text{ Vdc}$)	IEBO	-	0.1	μA	
DC Current Gain* ($I_C = 5 \text{ A}$, $V_{CE} = 5 \text{ Vdc}$) ($I_C = 20 \text{ A}$, $V_{CE} = 5 \text{ Vdc}$) ($I_C = 40 \text{ A}$, $V_{CE} = 5 \text{ Vdc}$)	hFE	25 10 5	- - -		
Collector-Emitter Saturation Voltage* ($I_C = 10 \text{ A}$, $I_B = 1 \text{ A}$) ($I_C = 20 \text{ A}$, $I_B = 4 \text{ A}$)	VCE(SAT)	- -	0.8 1.0	Vdc	
Base-Emitter Saturation Voltage* ($I_C = 10 \text{ A}$, $I_B = 1 \text{ A}$) ($I_C = 20 \text{ A}$, $I_B = 4 \text{ A}$)	VBE(SAT)	- -	1.0 0.8	Vdc	
Current Gain Bandwidth Product ($I_C = 1 \text{ A}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1 \text{ MHz}$)	fT	15	-	MHz	
Output Capacitance ($V_{CB} = 10 \text{ Vdc}$, $I_E = 0 \text{ A}$, $f = 1 \text{ MHz}$)	Cob	-	500	pf	
Delay Time	$I_C = 10 \text{ A}$ $I_{B1} = 1 \text{ A}$ $V_{BB} = -5 \text{ V}$ $R_{BB} = 0.6 \Omega$ $L_C = 0.25 \text{ mH}$ $V_{CLAMP} = 400 \text{ V}$	td	-	0.1	μs
Rise Time		tr	-	0.6	μs
Storage Time		ts	-	2.5	μs
Fall Time		tf	-	0.5	μs

*Pulse Test: Pulse Width = 300 μs , Duty Cycle = 2%

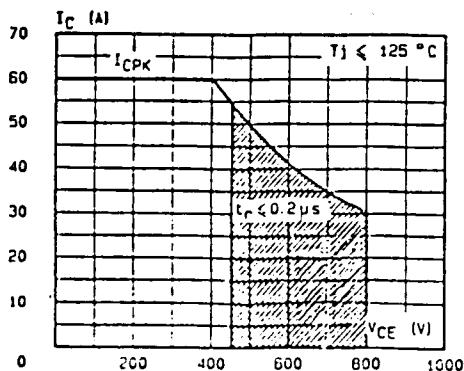


FIGURE 3: Forward biased safe operating area (FBSOA).

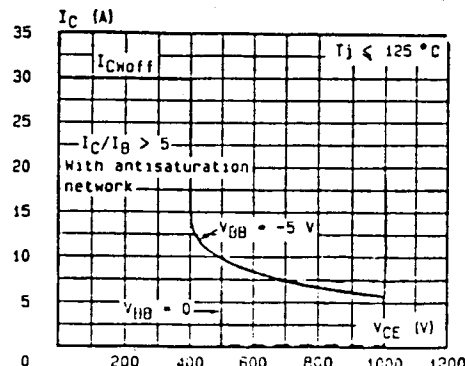


FIGURE 4: Reverse biased safe operating area (RBSOA).

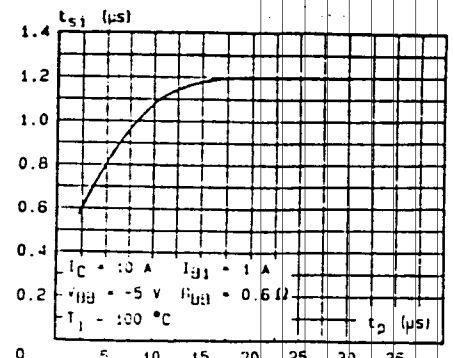


FIGURE 5: Carrier storage time versus pulse time (inductive load).

SSDI

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